

Fig. 3A

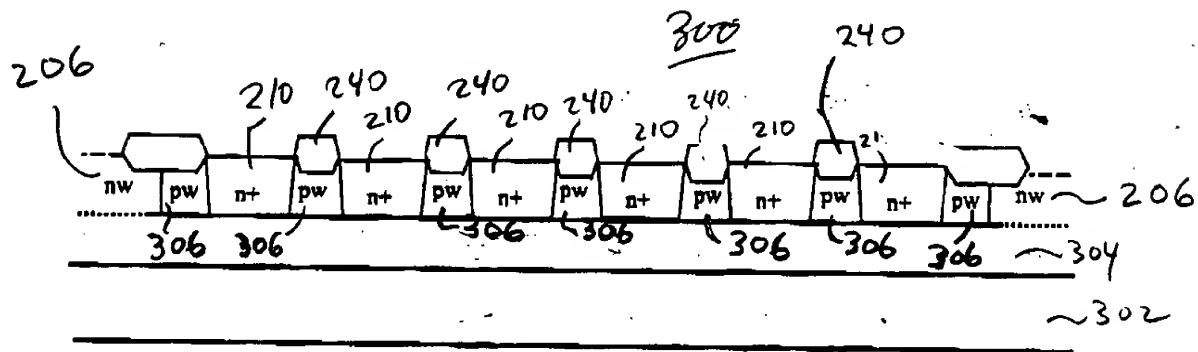


Fig. 3B

[illegible]

Fig. 4A

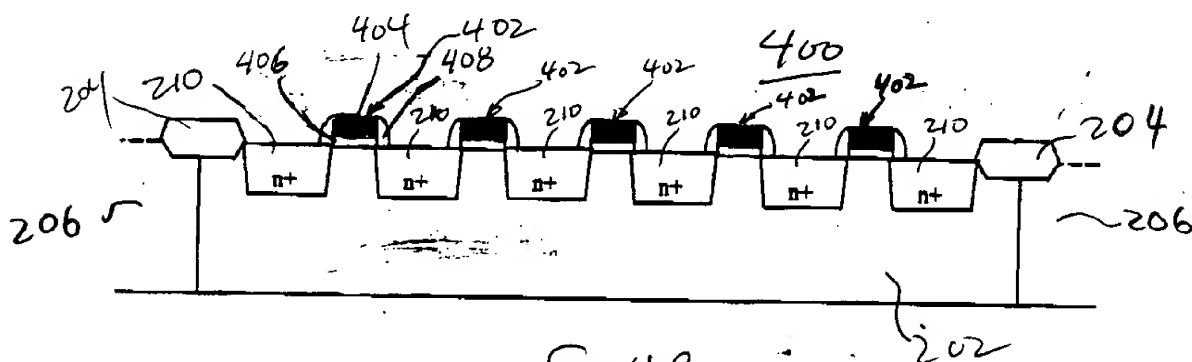


Fig. 4-B

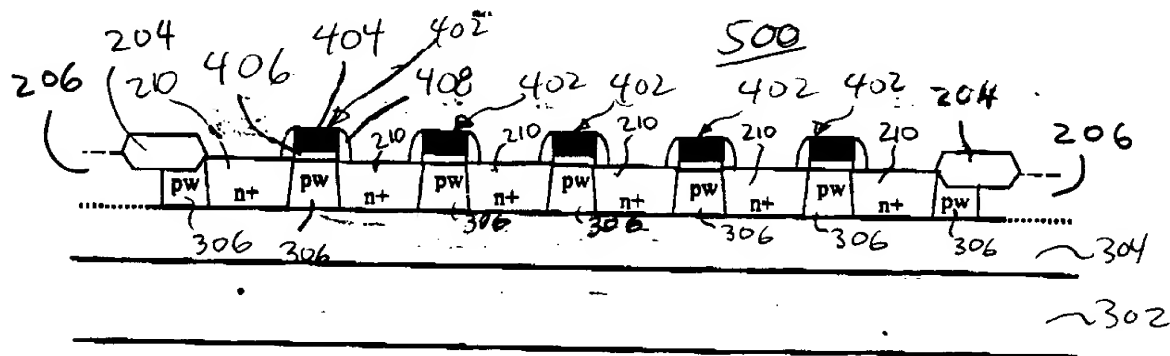
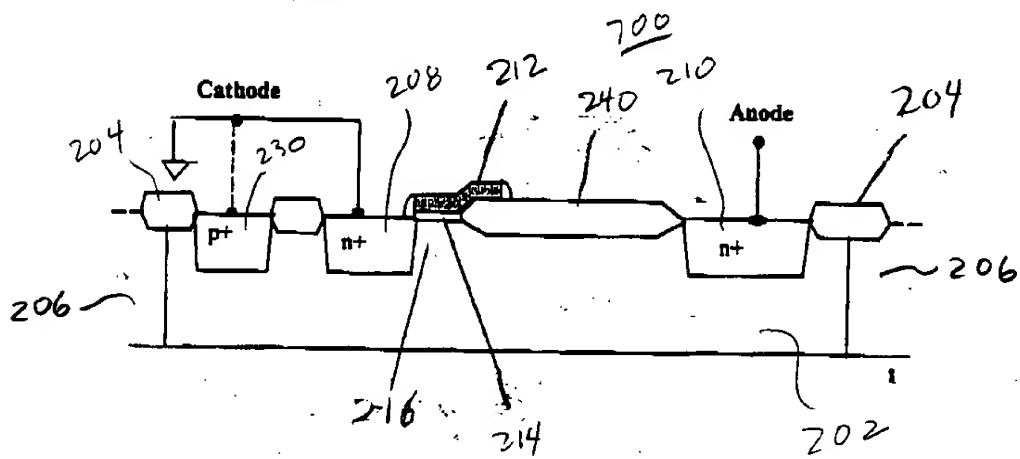
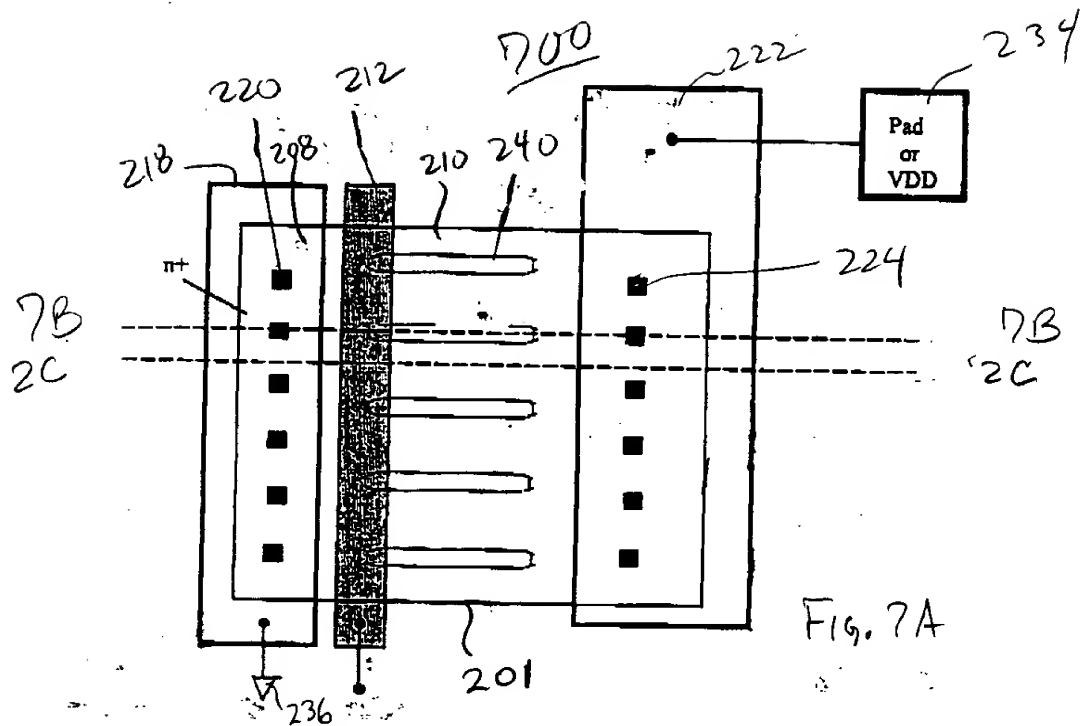


Fig. 5

FIG. 4C is a cross-sectional view of a semiconductor device. The device features a substrate with a series of regions labeled p+, n+, n+, and n+ from left to right. A Cathode is connected to the first p+ region, and an Anode is connected to the last n+ region. Various layers and contacts are labeled with numbers: 204, 206, 208, 212, 214, 215, 216, 230, 450, 452, 454, 456, 460, and 458. The device is shown in a cross-sectional view, with the Cathode and Anode terminals extending from the top surface.

FIG. 4D



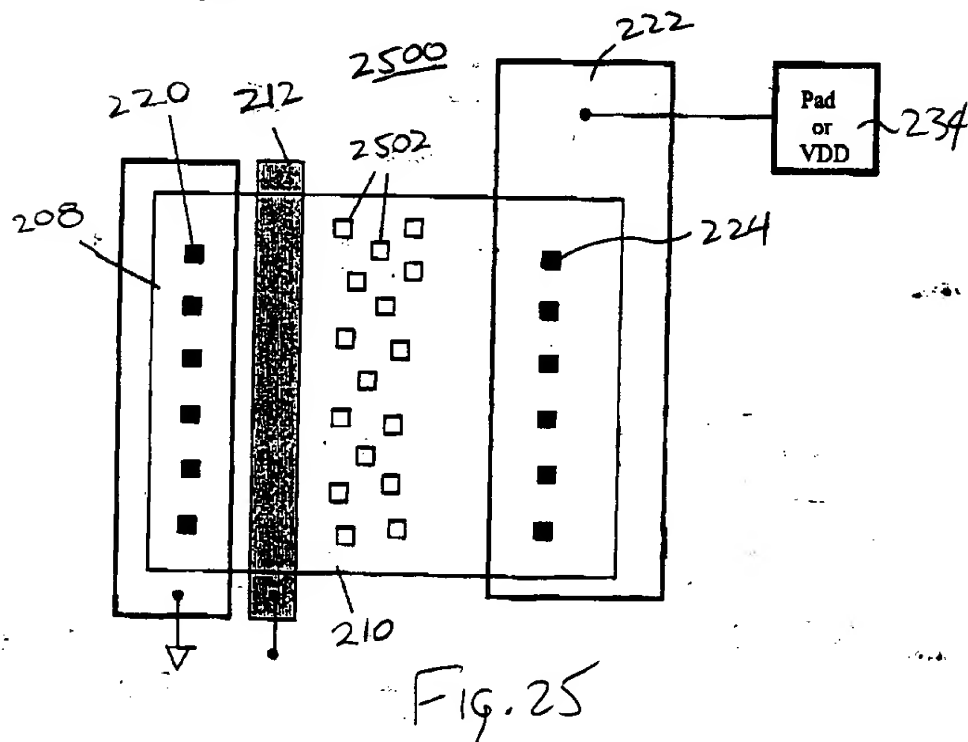
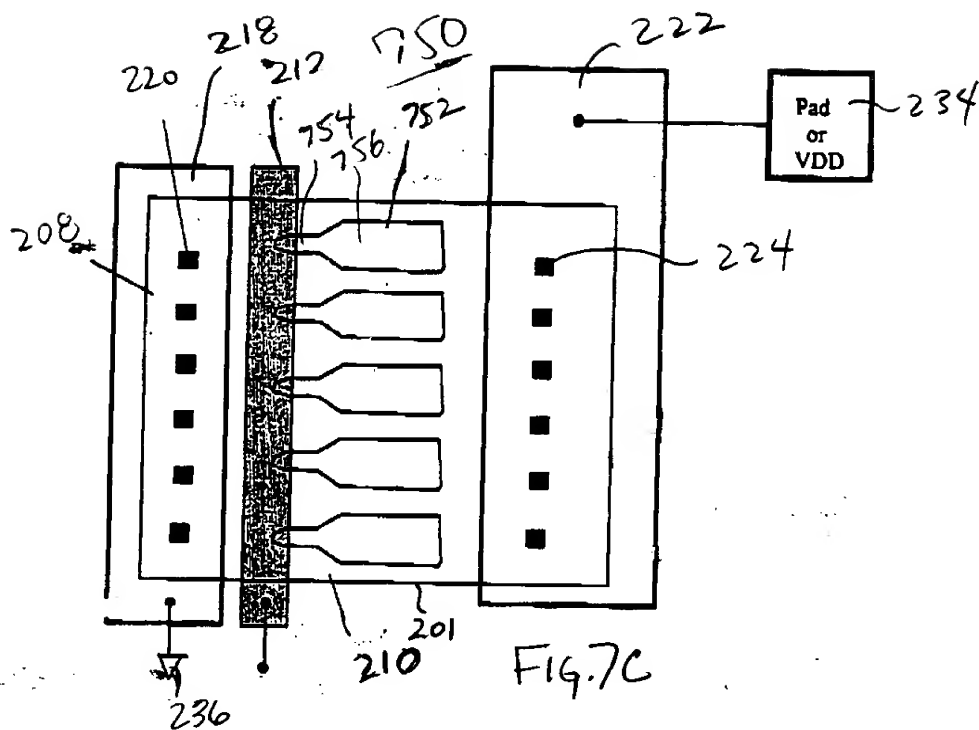
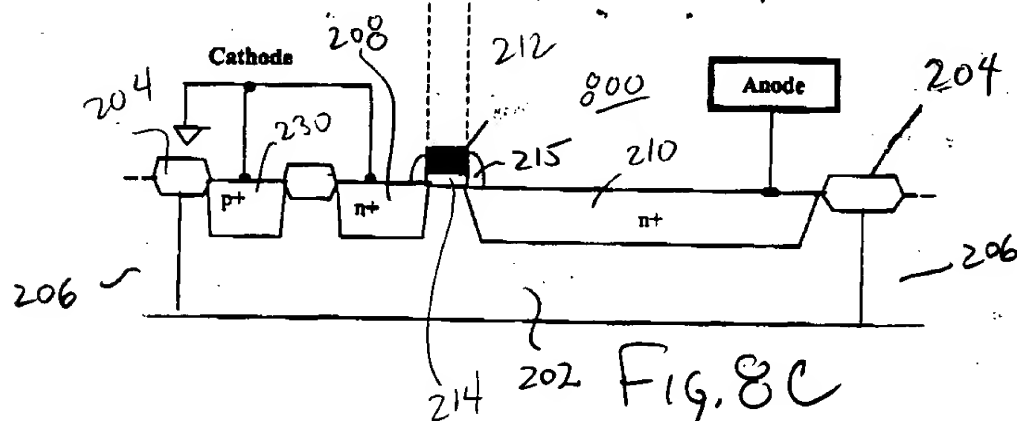
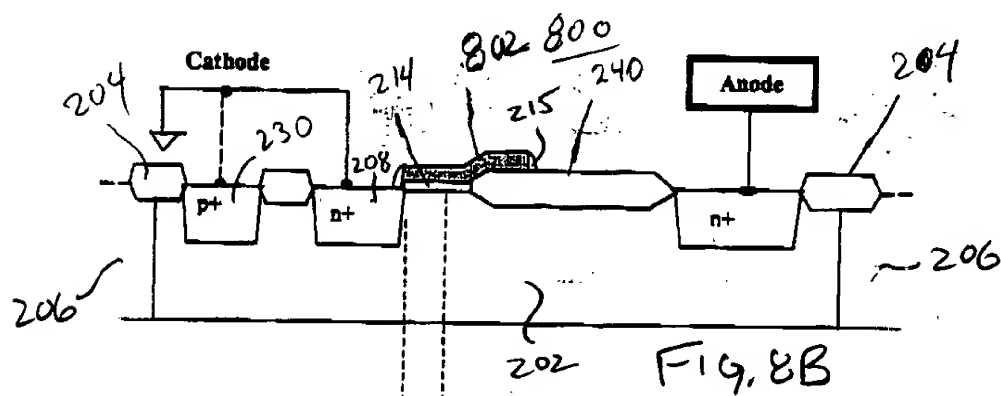
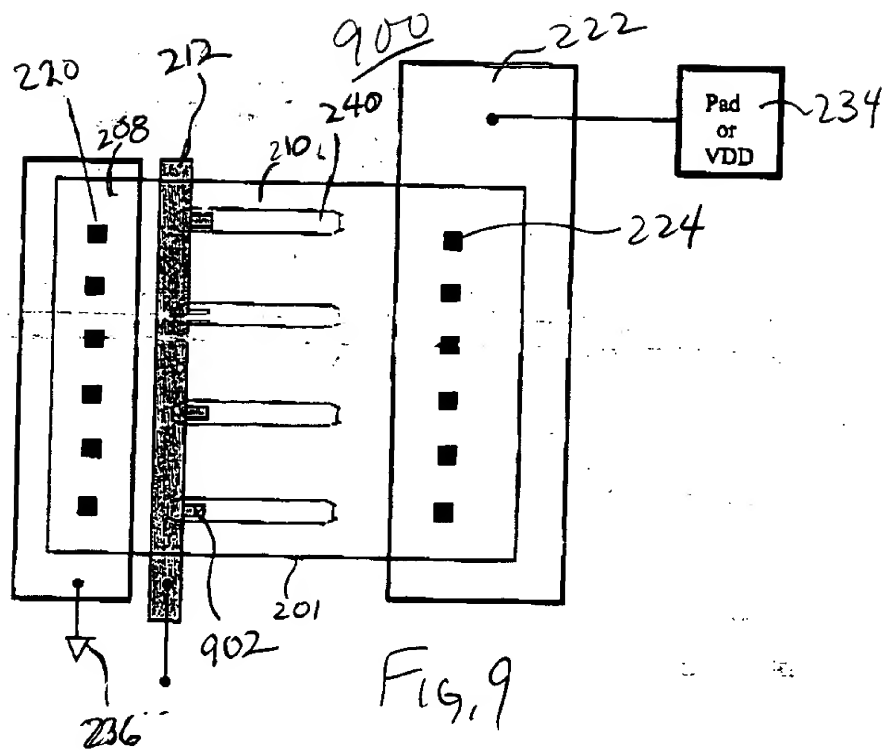
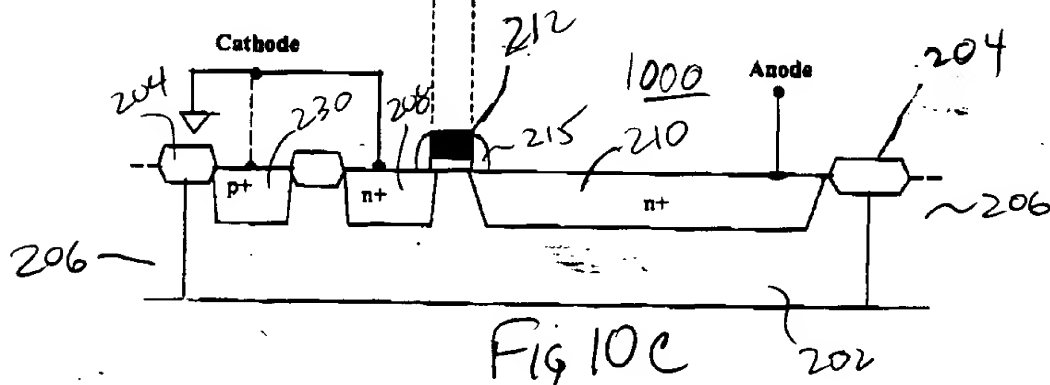
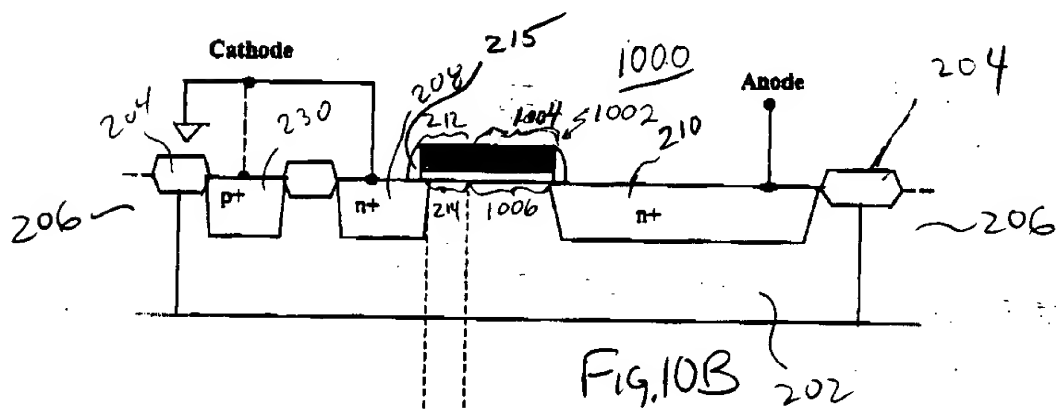
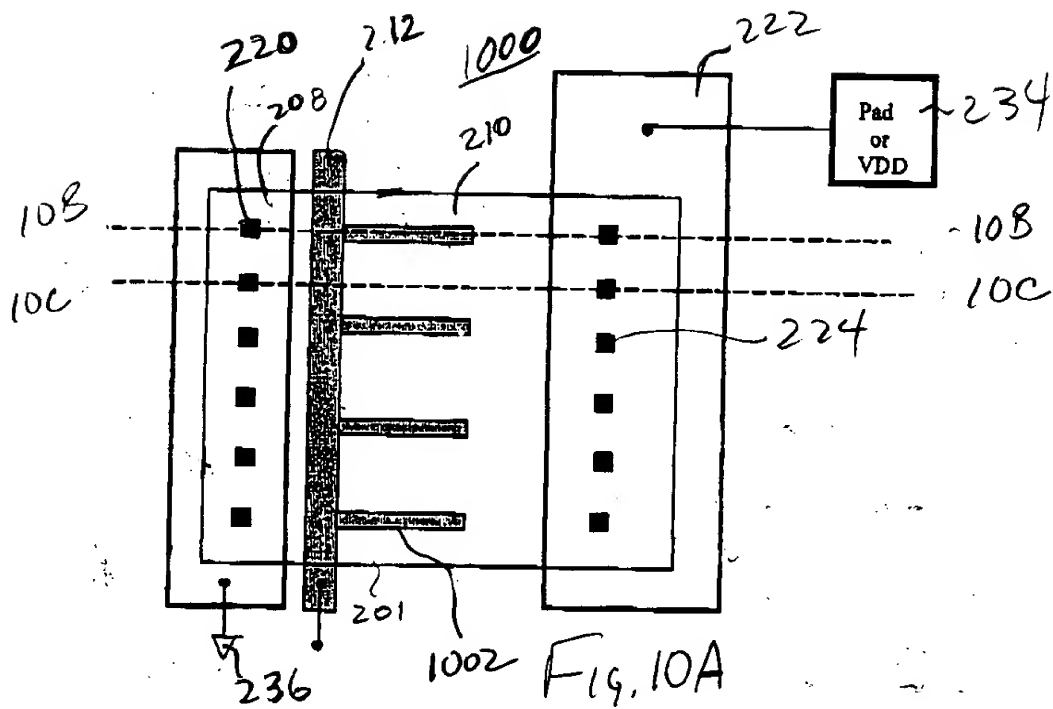


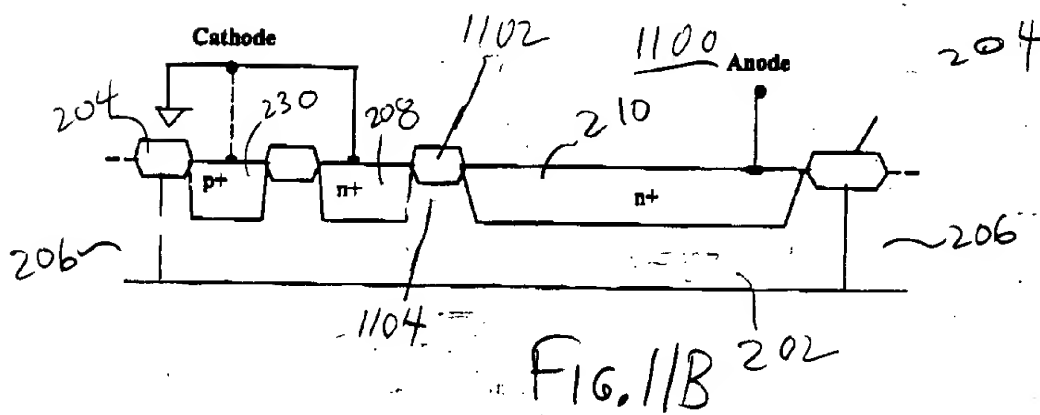
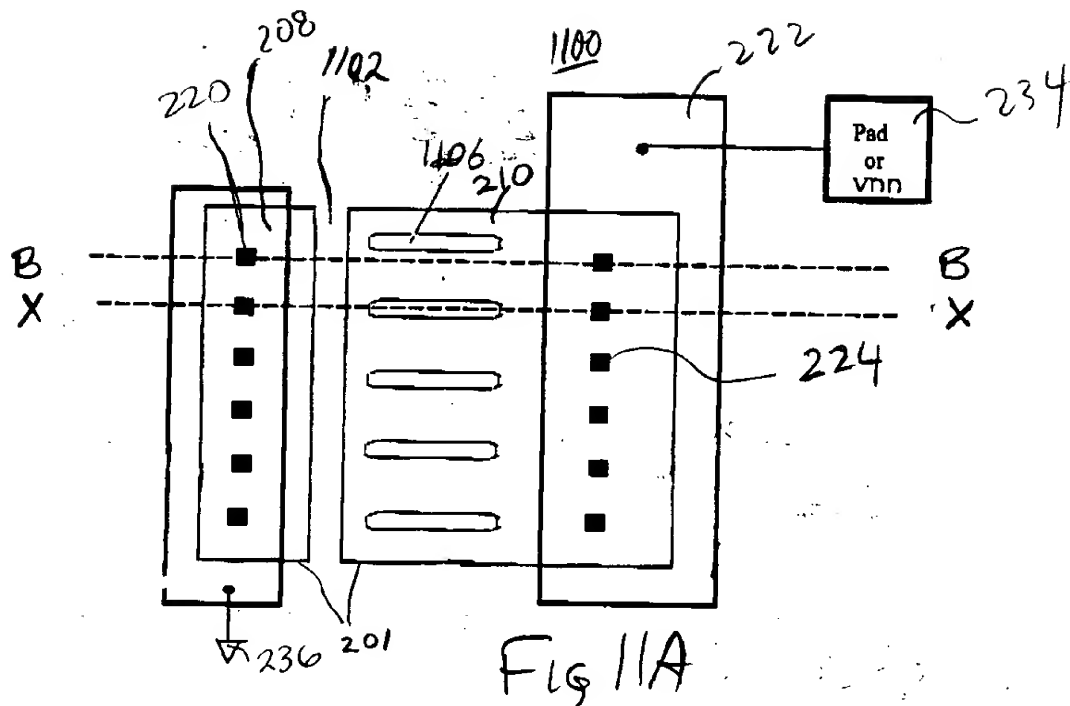
Fig. 8A

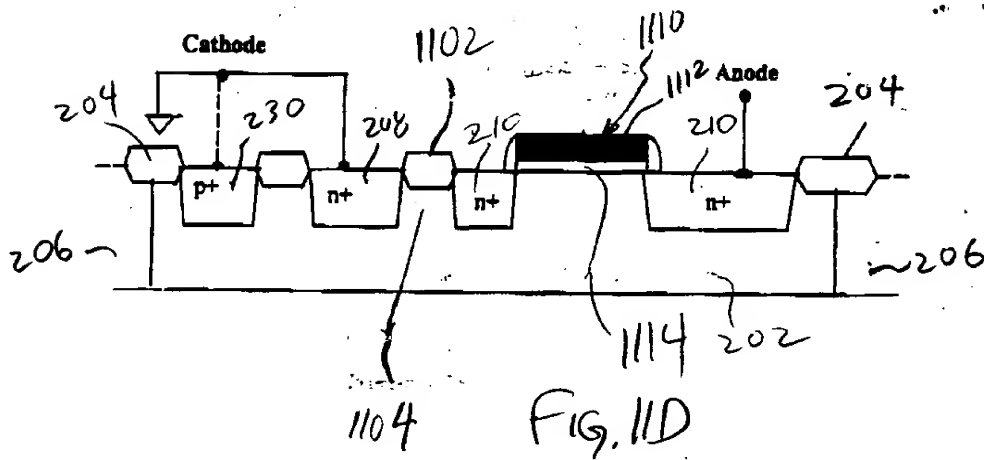
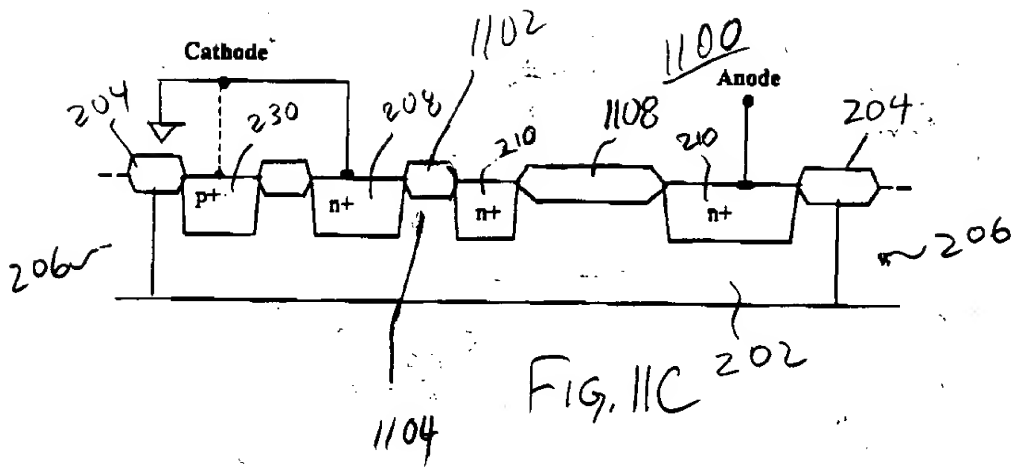




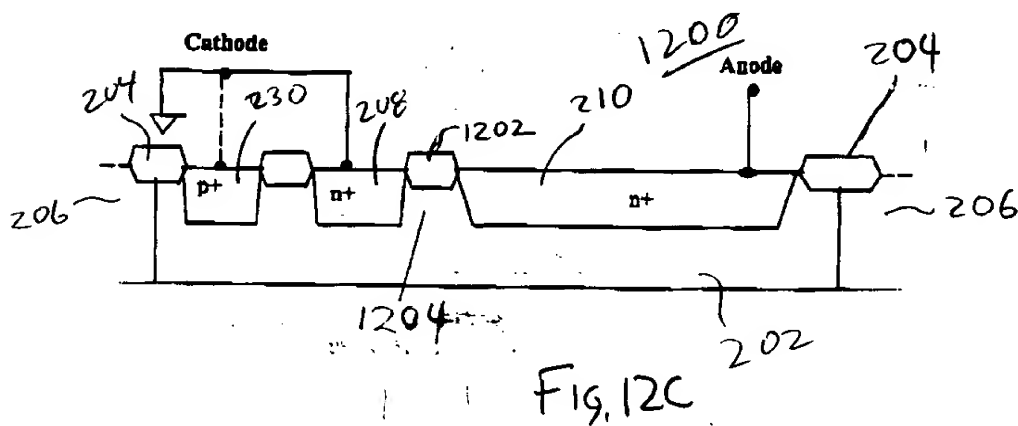
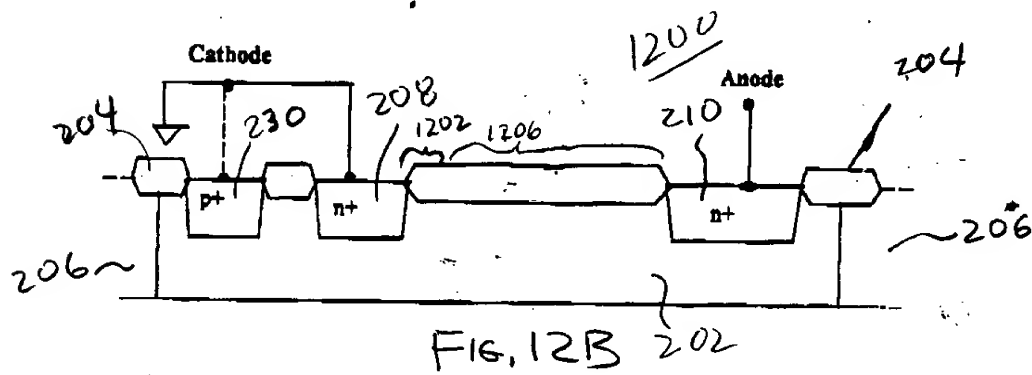
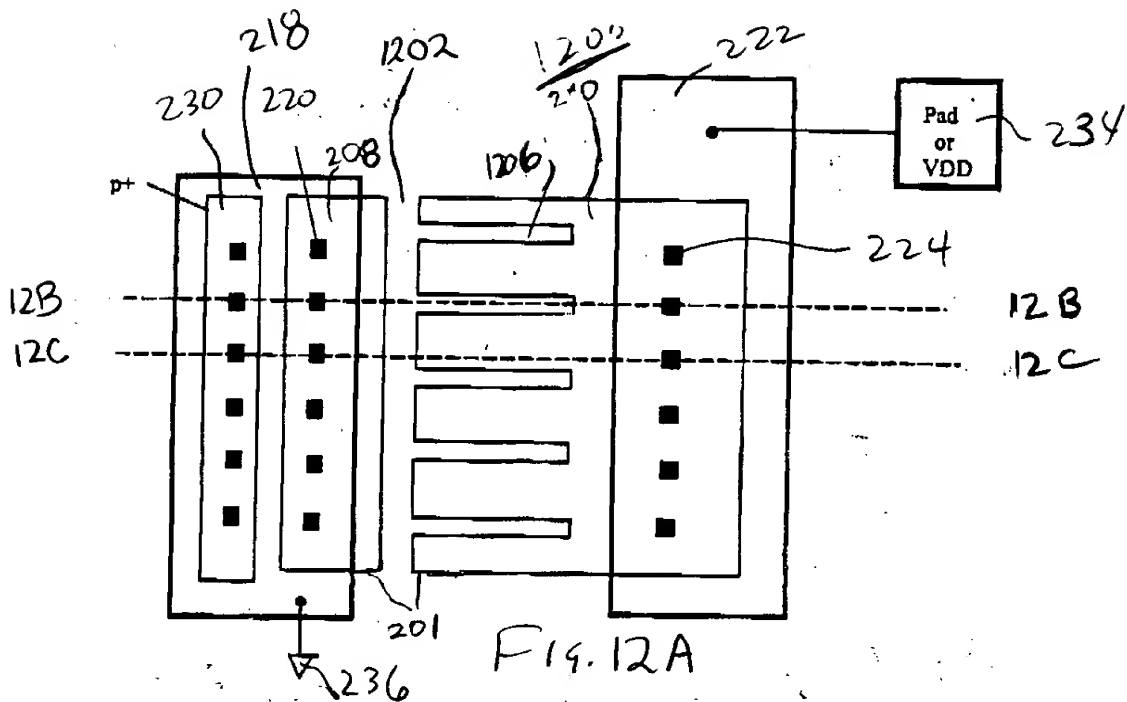
000377 57004260

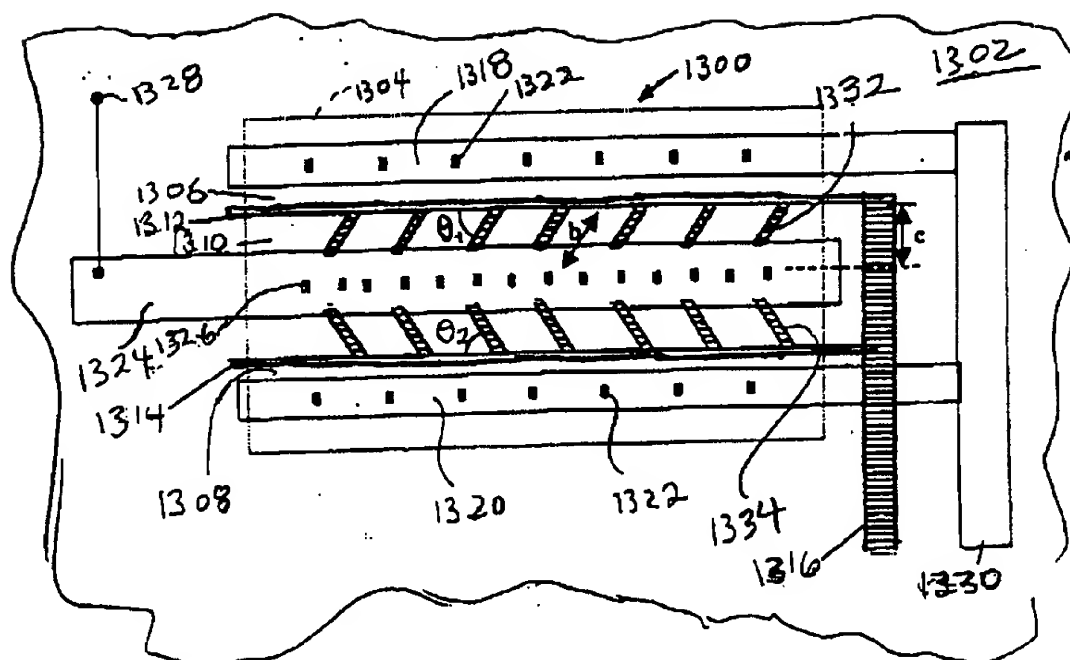






00000151007263





P.L. 12-14, 20

CHL
Dec. 14, 2001

WFC.

Dec. 14, 2001

WYU.

Dec. 16, 2008

Fig. 13

000001-97004200

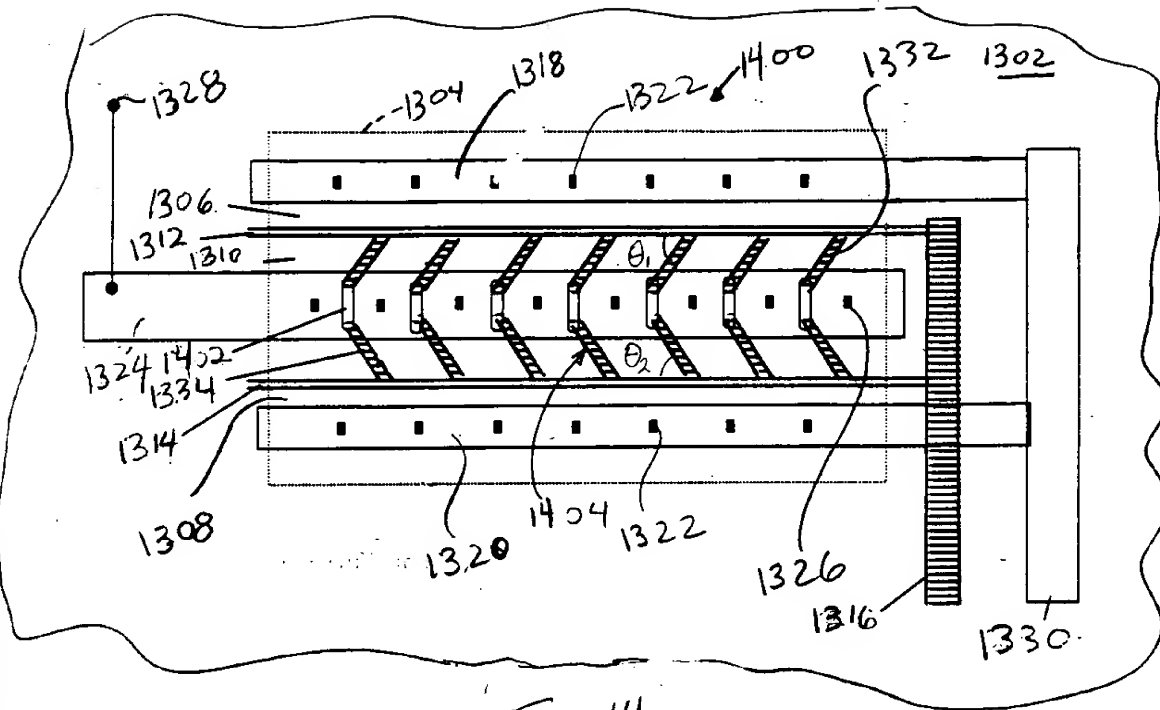


Fig. 14

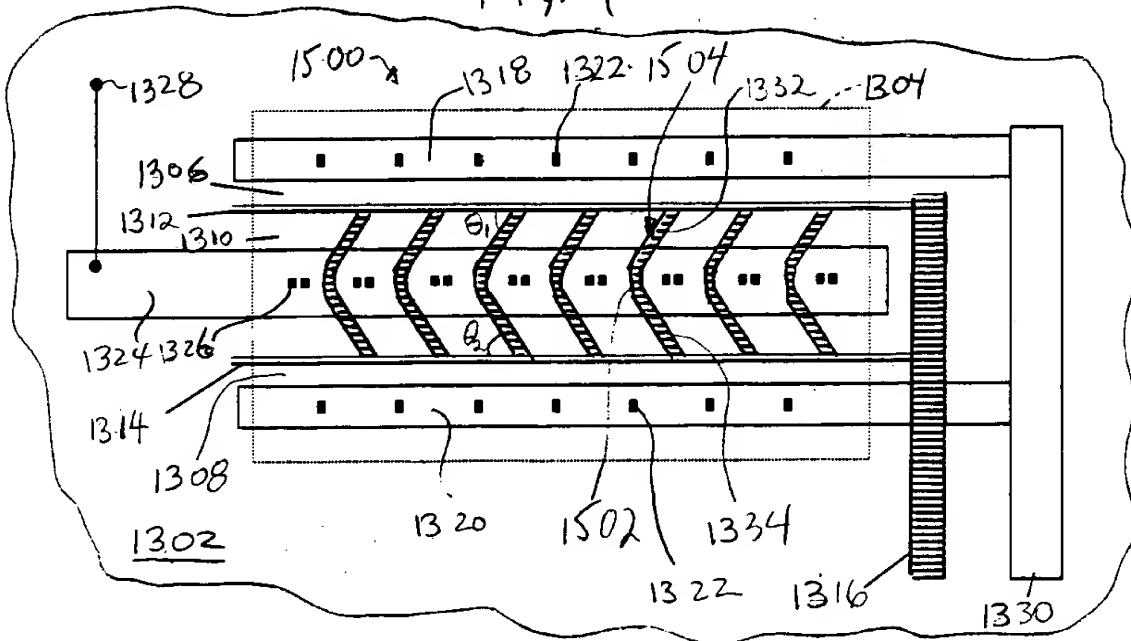


Fig. 15

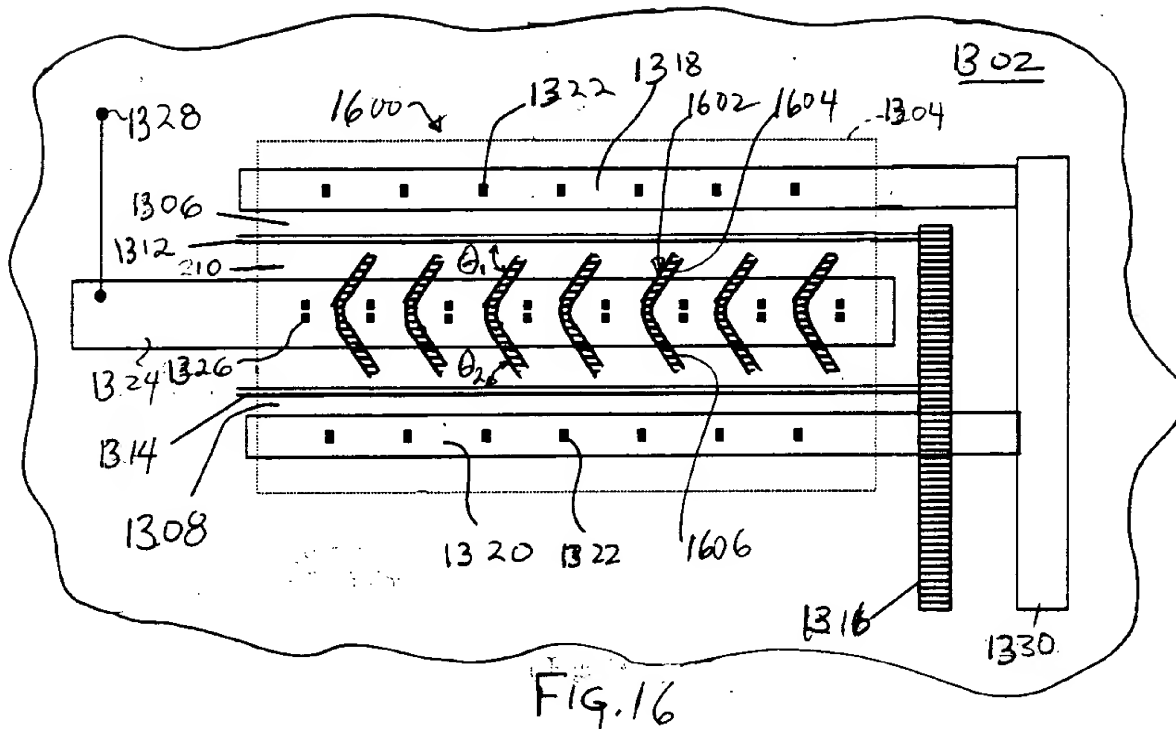
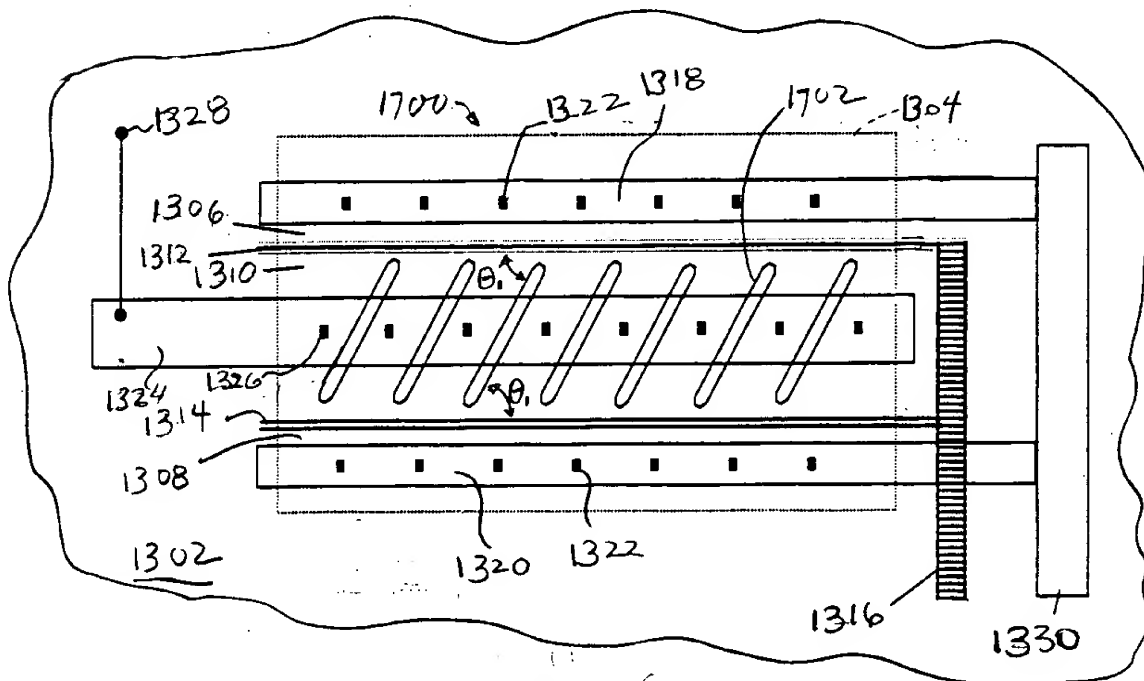


Fig. 17



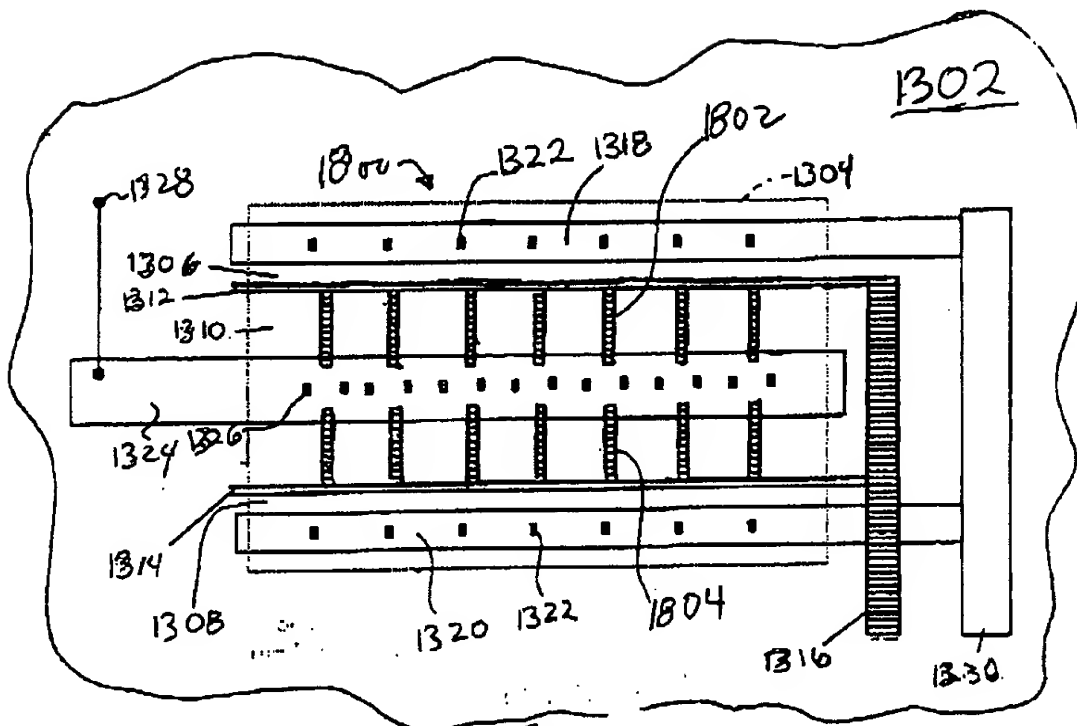


FIG. 18

S.d. 12-14, 2000
CHL. Dec. 14, 2000
WFC. Dec. 14, 2000
WYL. Dec. 16, 2000

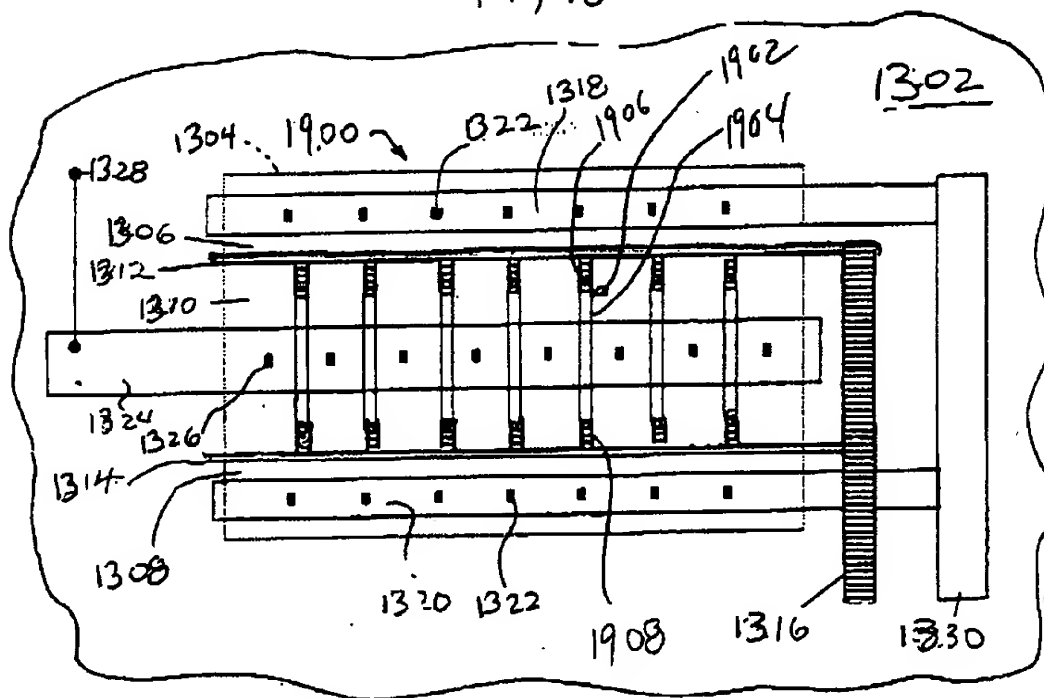


FIG. 19

S.d. 12-14, 2000
CHL. Dec. 14, 2000
WFC. Dec. 14, 2000
WYL. Dec. 16, 2000

000001-57004260

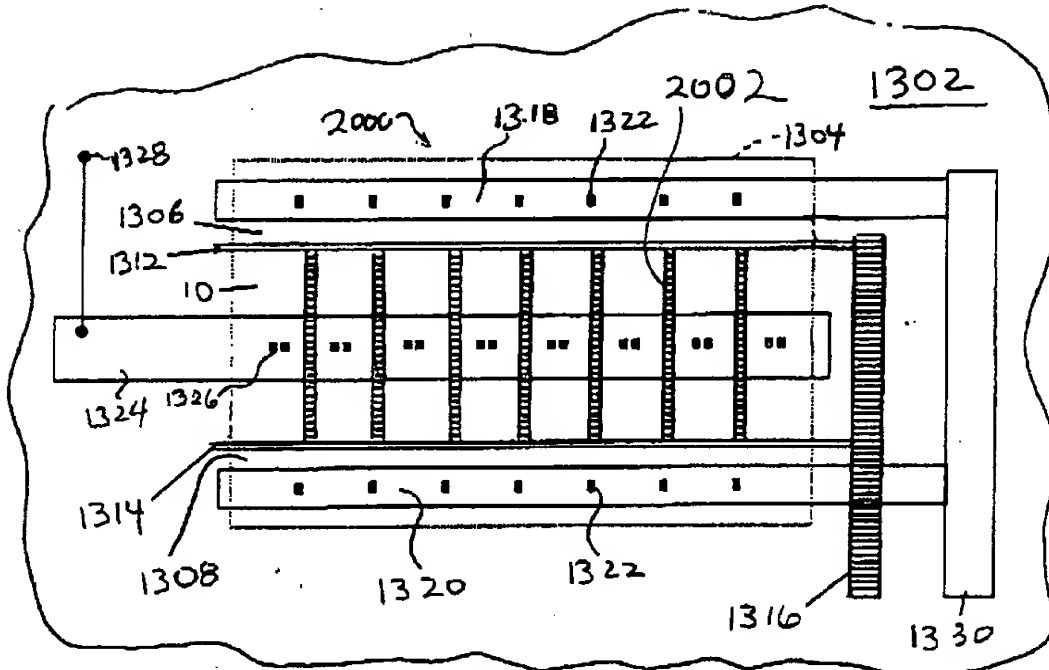


FIG. 20

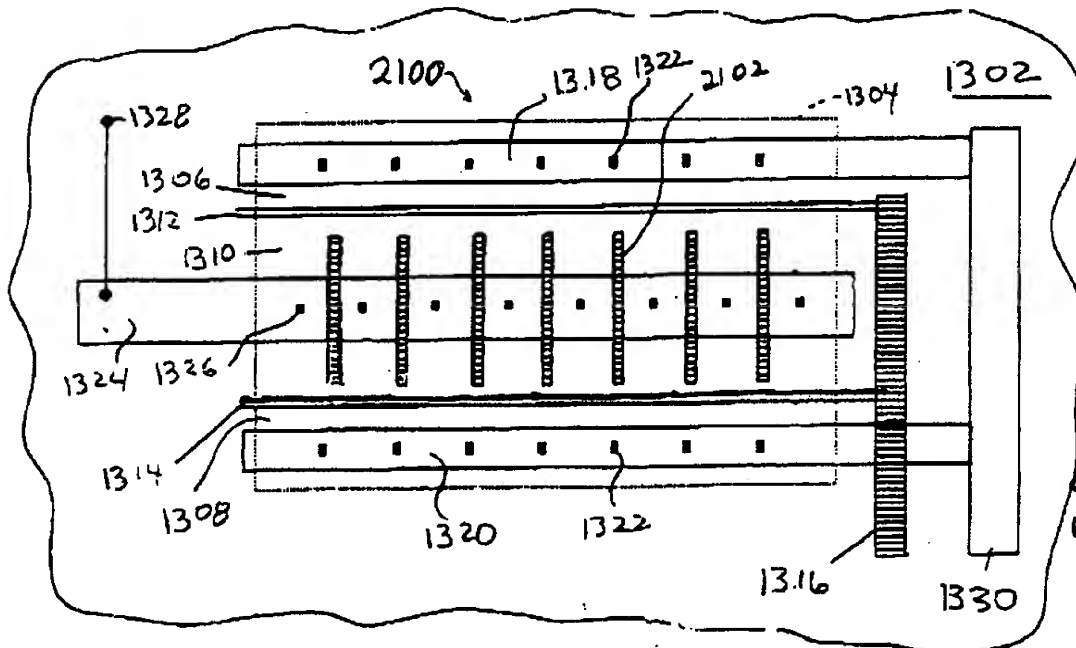


FIG. 21

S.R. 12-14, 2000
C.H.L. Dec. 14, 2000
L.F.C. Dec. 19, 2000
W.Y.L. Dec. 16, 2000

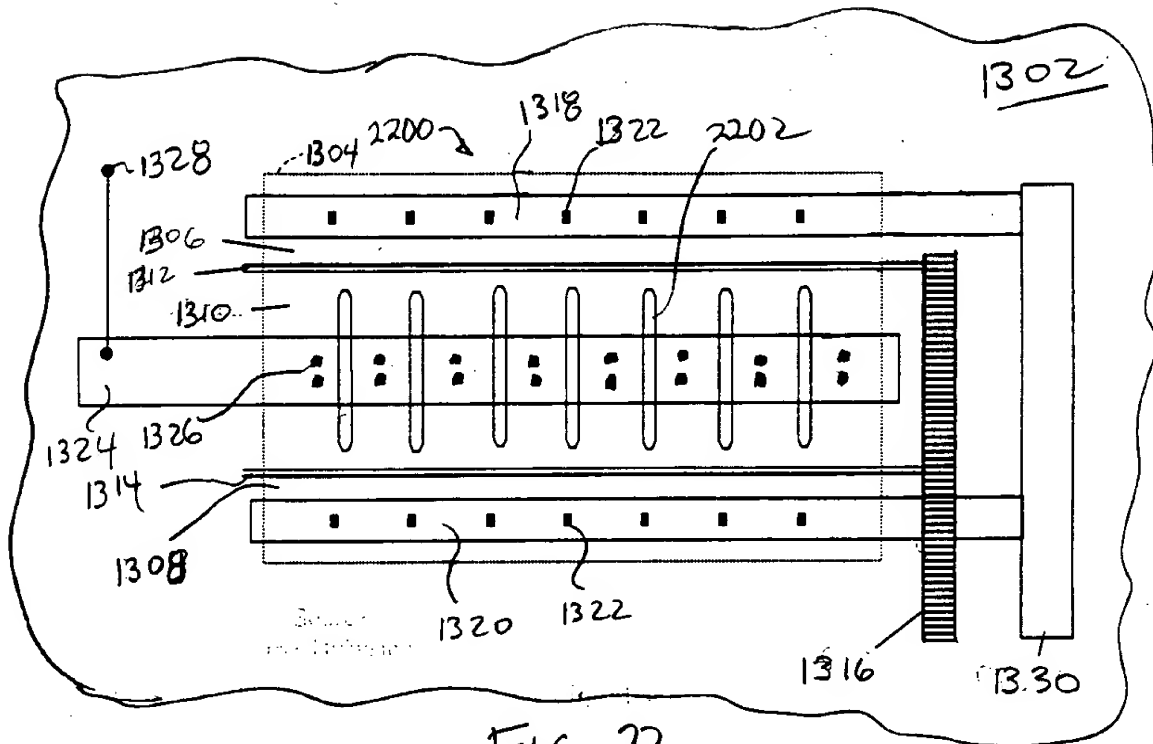


FIG. 22

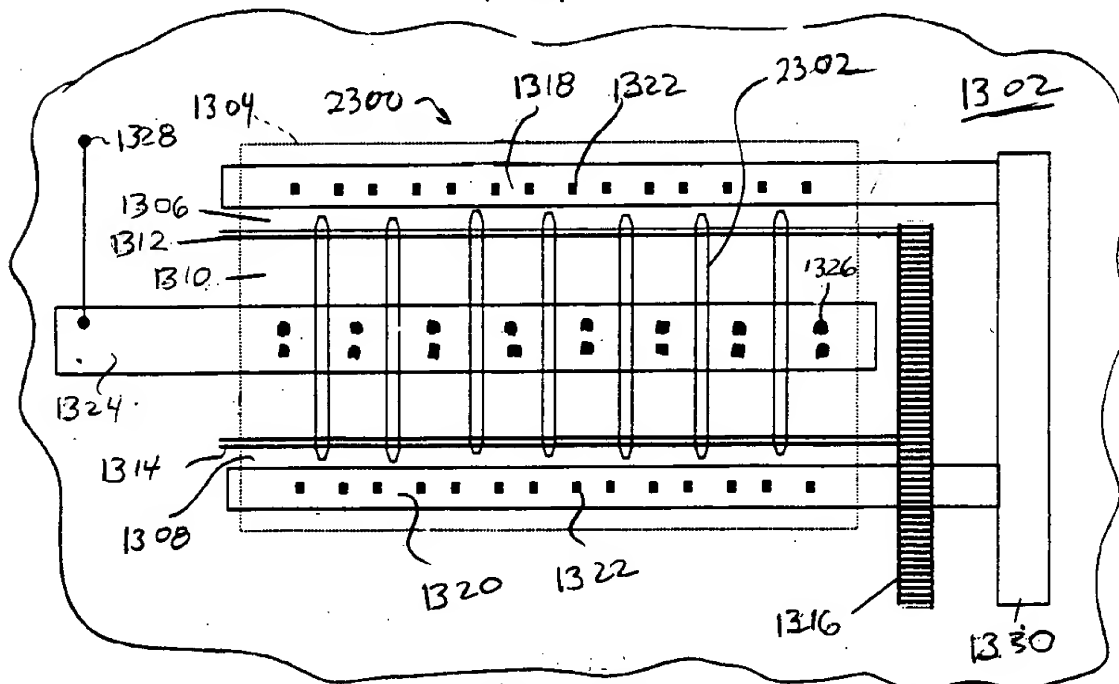


FIG. 23

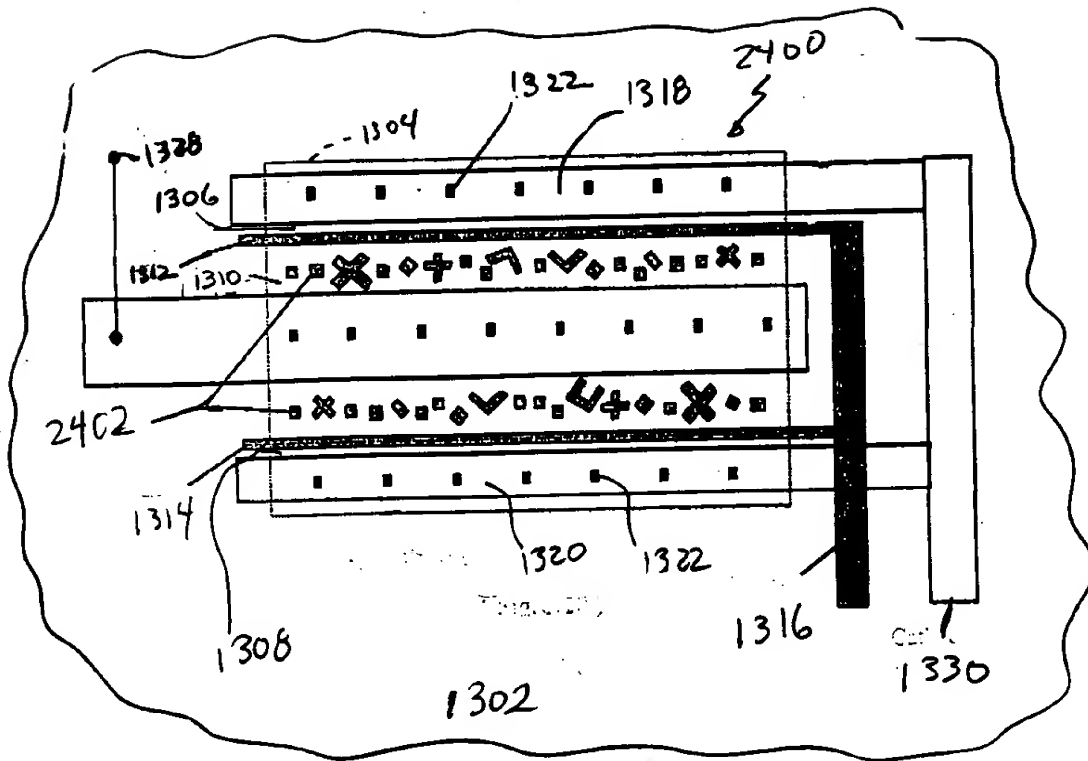


FIG. 24

SECRET 57004260

